

SB120E-G Thru. SB1100E-G

Voltage: 20 to 100 V

Current: 1.0 A

RoHS Device

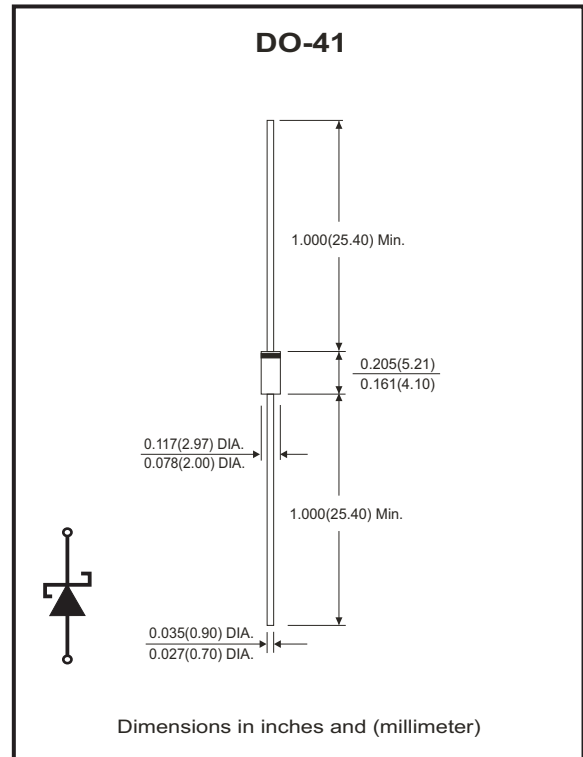


Features

- Low drop down voltage.
- 1.0A operation at TA=75°C with no thermal runaway.
- For use in low voltage, high frequency invertors free wheeling and polarity protection.
- Silicon epitaxial planar chips.
- ESD test under IEC6100-4-2 : Standard: >15KV(Air) & 8KV(Contact).
- Lead-free part, meet RoHS requirements.

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case: Molded plastic body DO-41
- Terminals: Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.34 grams(approx.).



Maximum Rating and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	SB 120E-G	SB 140E-G	SB 145E-G	SB 150E-G	SB 160E-G	SB 180E-G	SB 1100E-G	Unit
Maximum recurrent peak reverse voltage	V _{RRM}	20	40	45	50	60	80	100	V
Maximum RMS voltage	V _{RMS}	14	28	30	35	42	56	70	V
Maximum DC blocking voltage	V _{DC}	20	40	45	50	60	80	100	V
Maximum average forward rectified current 0.375" (9.5mm) lead length at TA=75°C, See Figure 1	I <sub(av)< sub=""></sub(av)<>	1.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method) TL=110°C	I _{FSM}	30							A
Maximum forward voltage at 1.0A (Note 1)	V _F	0.50		0.70		0.85		V	
Maximum DC reverse current At rated DC blocking voltage	I _R	0.5							mA
At TA=25°C TA=100°C		10		5					
Typical junction capacitance (Note 2)	C _J	110							pF
Typical thermal resistance (Note 3)	R _{θJA} R _{θJL}	80				30			°C/W
Operating junction temperature range	T _J	-65 to +125			-65 to +150				°C
Storage temperature range	T _{STG}	-65 to +150							°C

NOTES:

1. Pulse test : 300µs pulse width, 1% duty cycle.
2. Measured at 1.0MHz and applied reverse voltage of 4.0 Volts.
3. Thermal resistance from junction to ambient and from junction to lead P.C.B. mounted 0.375" (9.5mm) lead length

Company reserves the right to improve product design , functions and reliability without notice.

REV: B

RATING AND CHARACTERISTIC CURVES (SB120E-G Thru. SB1100E-G)

Fig.1 - Forward Current Derating Curve

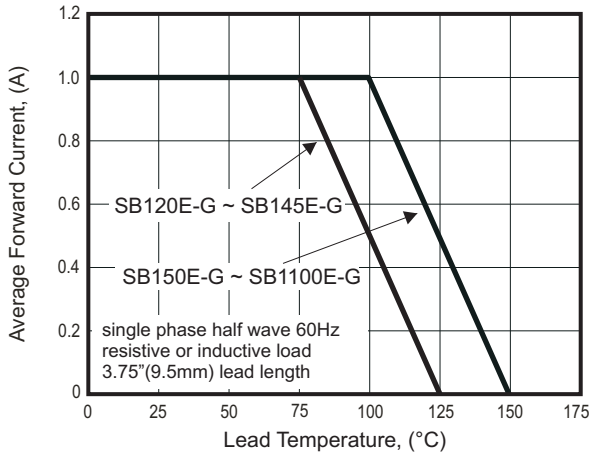


Fig.2 - Maximum Non-repetitive Peak Forward Surge Current

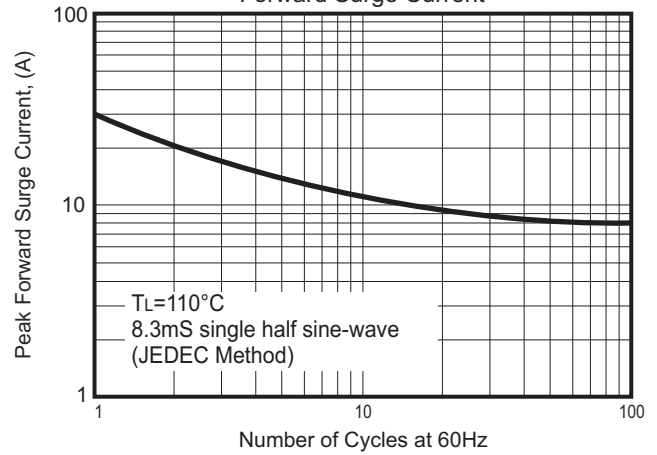


Fig.3 - Typical Instantaneous Forward Characteristics

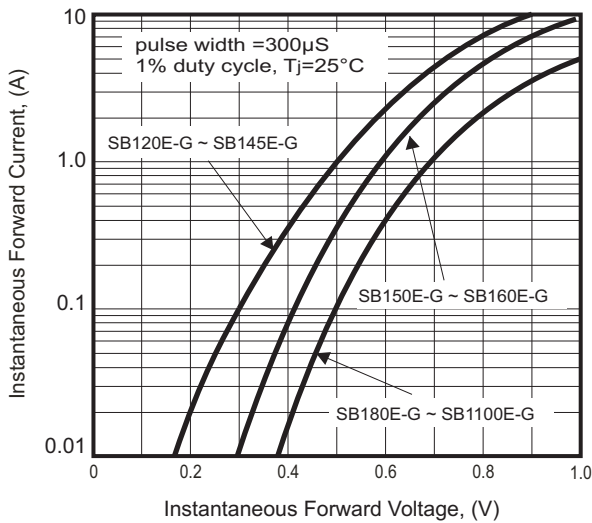


Fig.4A - Typical Reverse Characteristics

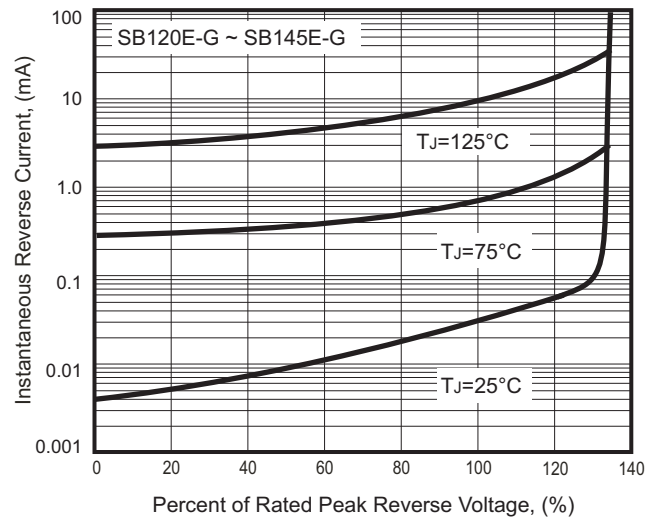


Fig.5 - Typical Junction Capacitance

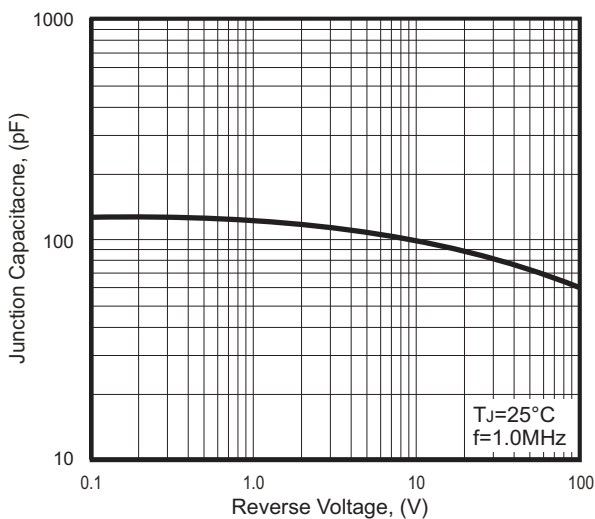
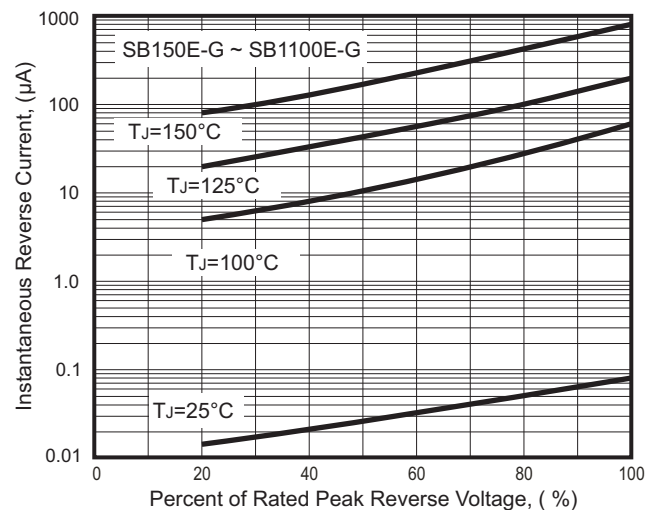


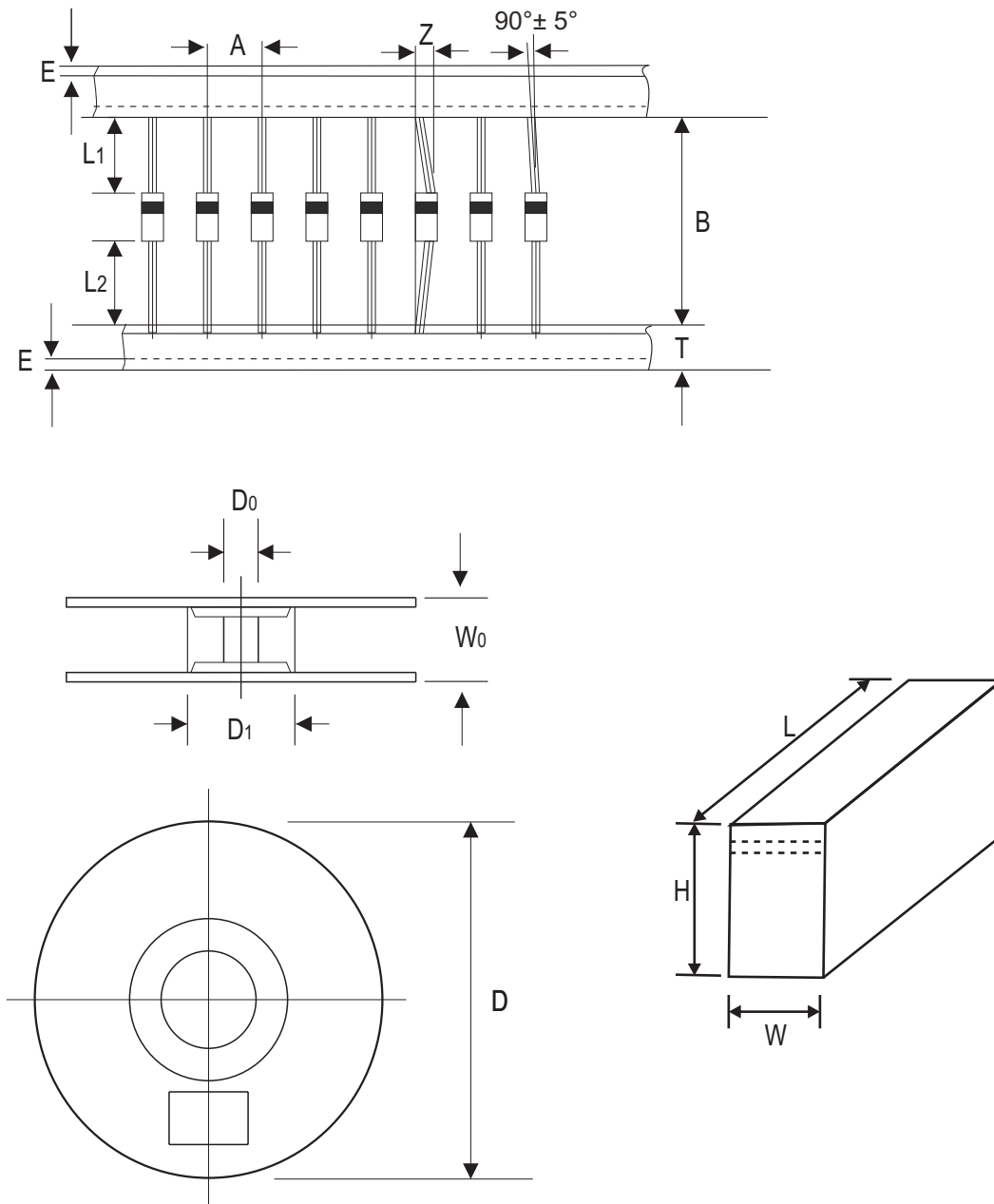
Fig.4B - Typical Reverse Characteristic



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Taping Specification For Axial Lead Diodes



DO-41	SYMBOL	A	B	Z	T	E	L1-L2
	(mm)	5.00 ± 0.50	52.40 ± 1.50	1.60 (max)	6.00 ± 0.40	3.00 (max)	1.00 (max)
	(inch)	0.197 ± 0.020	2.063 ± 0.059	0.063 (max)	0.236 ± 0.016	0.118 (max)	0.039 (max)

DO-41	SYMBOL	D1	D0	D	W0	L	W	H
	(mm)	82.20 ± 0.30	16.60 ± 0.40	330.00	77.00 ± 1.00	260.00 ± 5.00	75.00 ± 5.00	140.00 ± 5.00
	(inch)	3.236 ± 0.012	0.654 ± 0.016	12.992	3.031 ± 0.039	10.236 ± 0.197	2.953 ± 0.197	5.512 ± 0.197

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